Plastic-Encapsulate Diodes Schottky Rectifier

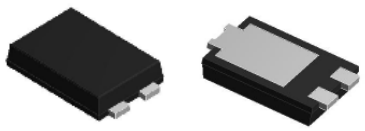
Features

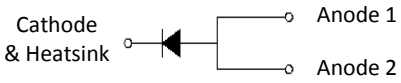
- I_O 10A
- VRRM 100V
- High surge current capability
- Low Vf

Applications

- Rectifier

TO-277





Limiting Values (Absolute Maximum Rating)

Item	Symbol	Unit	Conditions	AS10J100T
Repetitive Peak Reverse Voltage	V_{RRM}	V		100
Maximum RMS Voltage	V_{RMS}	V		70
Average Forward Current	$I_{F(AV)}$	A	60Hz Half-sine wave, Resistance load, TL=125℃	10
Surge(Non-repetitive)Forward Current	I_{FSM}	A	60Hz Half-sine wave,1 cycle, Ta=25℃	200
Junction Temperature	T_J	℃		-55~+150
Storage Temperature	T_{STG}	℃		-55~+150

Electrical Characteristics (T_a=25℃ Unless otherwise specified）

Item	Symbol	Unit	Test Condition		AS10J100T
Peak Forward Voltage	V_F	V	IF=10A	T_a=25℃	0.59(TYP) 0.64(MAX)
				T_a=125℃	0.57(TYP) 0.62(MAX)
Peak Reverse Current	I_{RRM1}	mA	$V_{RM}=V_{RRM}$	T_a=25℃	0.015(TYP) 0.05(MAX)
	I_{RRM2}			T_a=125℃	12(TYP) 20(MAX)
Thermal Resistance(Typical)	$R_{\theta J-A}$	℃/W	Between junction and ambient		80
	$R_{\theta J-L}$		Between junction and lead		5
Typical junction capacitance	C_J	pF	4.0 V, 1 MHz		240

Plastic-Encapsulate Diodes Schottky Rectifier

Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

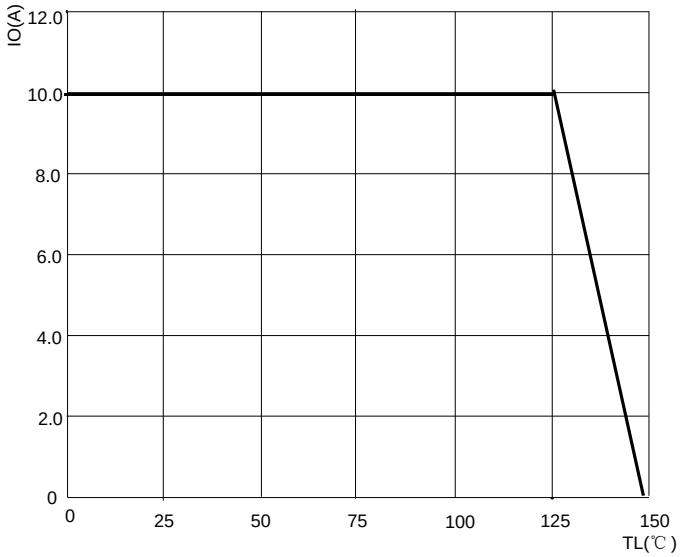


FIG.2: MAXIMUM NON-REPETITIVE FORWARD URGE CURRENT

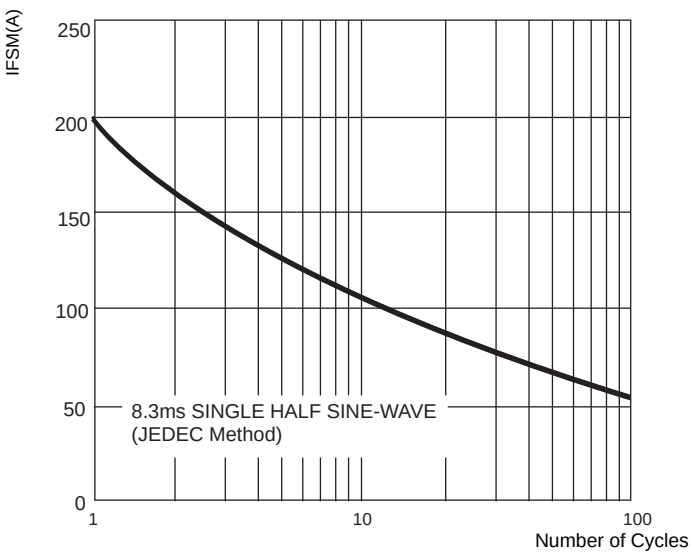


FIG3：Forward Voltage

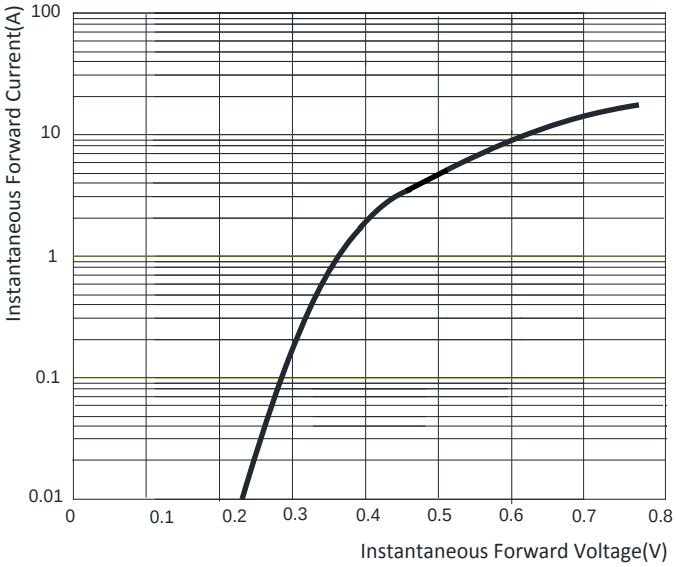
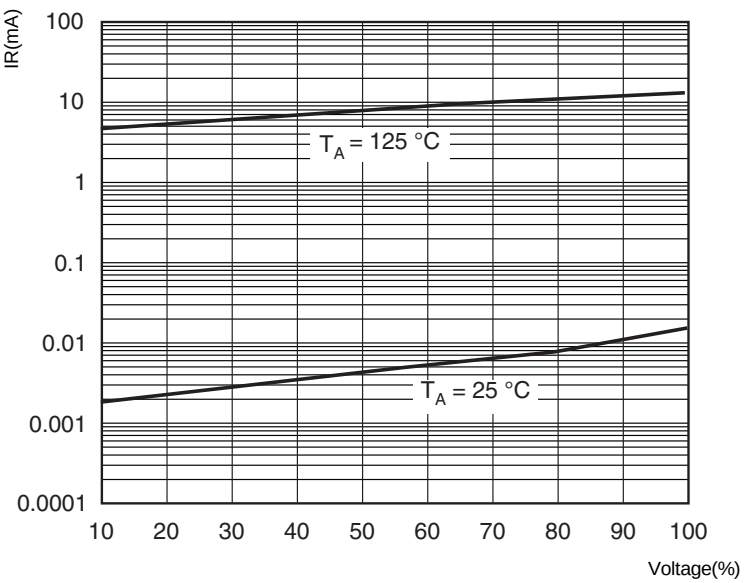
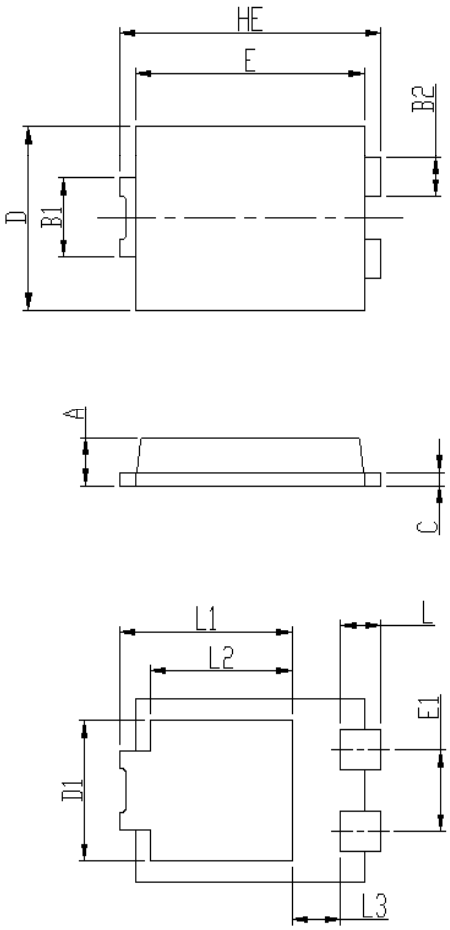


FIG.4：TYPICAL REVERSE CHARACTERISTICS



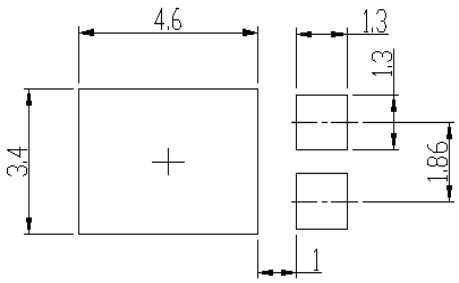
Plastic-Encapsulate Diodes Schottky Rectifier

TO- 277 Package Outline Dimensions



DIM	Unit: mm		Unit: inch	
	MIN	MAX	MIN	MAX
HE	6.4	6.6	0.252	0.260
E	5.6	5.8	0.220	0.228
D	4.1	4.3	0.161	0.169
B1	1.7	1.9	0.067	0.075
B2	0.8	1	0.031	0.039
A	1.05	1.2	0.041	0.047
C	0.3	0.4	0.012	0.016
L	0.85	1.1	0.033	0.043
L1	4.2	4.4	0.165	0.173
L2	3.52 Typ.		0.139 Typ.	
L3	1.1	1.4	0.043	0.055
D1	3	3.3	0.118	0.130
E1	1.86 Typ.		0.073 Typ.	

TO- 277 Suggested Pad Layout



Note:
1.Controlling dimension:in millimeters.
2.General tolerance:± 0.05mm.
3.The pad layout is for reference purposes only.